





#### P-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

### **Features**

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 2)
- **ESD Protected Gate**
- "Green" Device (Note 4)
- Qualified to AEC-Q101 standards for High Reliability

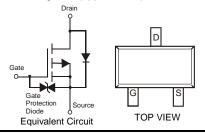
# **Mechanical Data**

- Case: SOT-523
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.002 grams (approximate)









# Maximum Ratings @T<sub>A</sub> = 25°C unless otherwise specified

Chara	acteristic		Symbol	Value	Units	
Drain-Source Voltage			$V_{DSS}$	-20	V	
Gate-Source Voltage			$V_{GSS}$	±8	V	
Drain Current (Note 1)	Steady State	$T_A = 25$ °C $T_A = 85$ °C	I <sub>D</sub>	-430 -310	mA	
Pulsed Drain Current (Note 3)			I <sub>DM</sub>	-750	mA	

### **Thermal Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 1)	$P_D$	150	mW
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	833	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

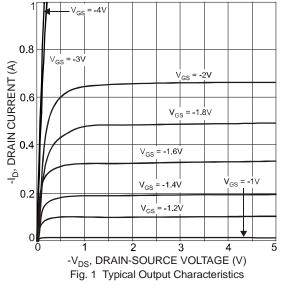
### **Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

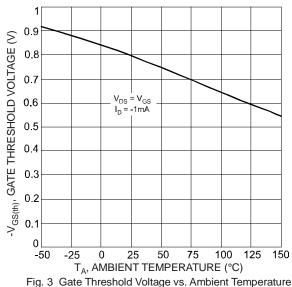
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 5)								
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	_	_	V	$V_{GS} = 0V, I_D = -250mA$		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	-1.0	μΑ	$V_{DS} = -20V, V_{GS} = 0V$		
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±1.0	μΑ	$V_{GS} = \pm 4.5V, V_{DS} = 0V$		
ON CHARACTERISTICS (Note 5)								
Gate Threshold Voltage	V <sub>GS(th)</sub>	-0.5		-1.0	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$		
			0.7	1.1		$V_{GS} = -4.5V$ , $I_D = -430mA$		
Static Drain-Source On-Resistance	R <sub>DS (ON)</sub>	_	1.1	1.6	Ω	$V_{GS} = -2.5V$ , $I_D = -300mA$		
	, ,		1.7	2.4		$V_{GS} = -1.8V, I_D = -150mA$		
Forward Transfer Admittance	Y <sub>fs</sub>	200	_	_	ms	$V_{DS} = 10V, I_D = 0.2A$		
Diode Forward Voltage (Note 5)	$V_{SD}$	_	_	-1.4	V	$V_{GS} = 0V, I_{S} = -115mA$		
DYNAMIC CHARACTERISTICS								
Input Capacitance	C <sub>iss</sub>	_	_	175	pF	101/11/ 01/		
Output Capacitance	Coss	_	_	30	pF	$V_{DS} = -16V, V_{GS} = 0V$ - f = 1.0MHz		
Reverse Transfer Capacitance	C <sub>rss</sub>	_	_	20	pF	1 = 1.0WHZ		

Notes:

- Device mounted on FR-4 PCB.
- No purposefully added lead.
- Pulse width ≤10μS, Duty Cycle ≤1% 3.
- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.
- Short duration pulse test used to minimize self-heating effect.







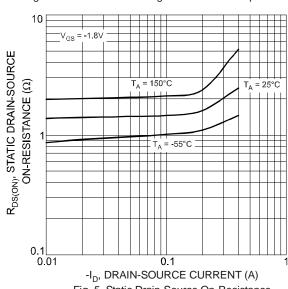
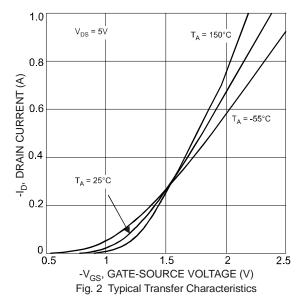


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current



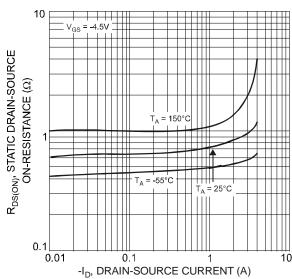


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

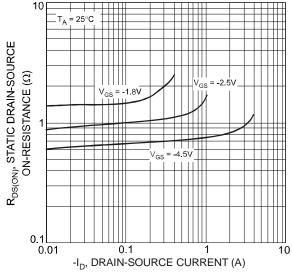


Fig. 6 Static Drain-Source On-Resistance vs. Drain-Source Current



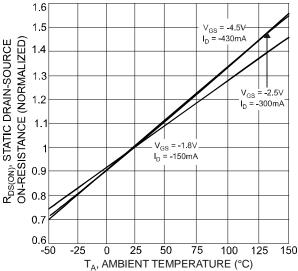


Fig. 7 Static Drain-Source On-State Resistance vs. Ambient Temperature

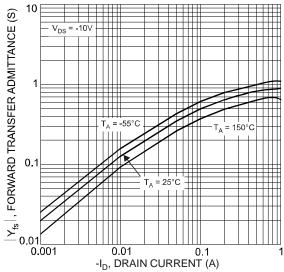


Fig. 9 Forward Transfer Admittance vs. Drain Current

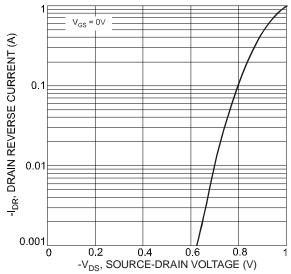
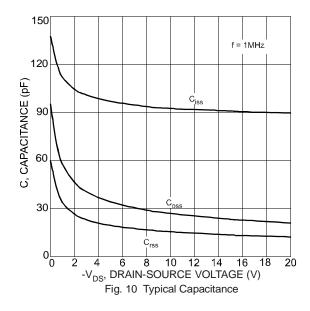


Fig. 8 Reverse Drain Current vs. Source-Drain Voltage

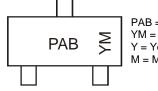


# Ordering Information (Note 6)

Part Number	Case	Packaging		
DMP2004TK-7	SOT-523	3000/Tape & Reel		

Notes: 6. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

# Marking Information



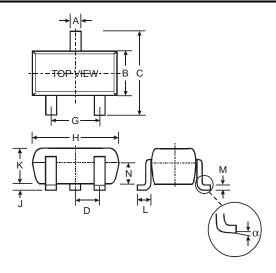
PAB = Product Type Marking Code YM = Date Code Marking Y = Year ex: T = 2006 M = Month ex: 9 = September

Date Code Key

Year	200	6	2007		2008	20	09	2010		2011	2	2012
Code	Т		U		V	٧	٧	Χ		Υ		Z
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

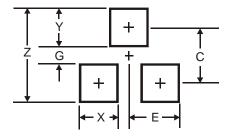


# **Package Outline Dimensions**



	SOT-523					
Dim	Min	Max	Тур			
Α	0.15	0.30	0.22			
В	0.75	0.85	0.80			
С	1.45	1.75	1.60			
D	_		0.50			
G	0.90	1.10	1.00			
Н	1.50	1.70	1.60			
J	0.00	0.10	0.05			
K	0.60	0.80	0.75			
L	0.10	0.30	0.22			
M	0.10	0.20	0.12			
N	0.45	0.65	0.50			
α	0°	8°				
All	All Dimensions in mm					

# **Suggested Pad Layout**



Dimensions	Value (in mm)
Z	1.9
G	0.9
Х	0.5
Y	0.5
С	1.4
E	0.5

#### IMPORTANT NOTICE

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